

PULSED LASER DIODES

905 nm

part number	specifications (@ 21°C, 150 ns, 6.66kHz)					
	wavelength	min power	package	emitting area	lop	lth
	nm	Watt		µm x µm	A	mA
905D1S1.5X	905	3	U,S	37.5 x 1	3,5	100
905D1S03X	905	6	U,S	75 x 1	7	200
905D1S06X	905	13	U,S	150 x 1	15	400
905D1S09X	905	19	U,S	230 x 1	22	600
905D1S12X	905	26	U,S	300 x 1	30	800
905D1S16X	905	34	U,S	400 x 1	40	1200
905D2S06X	905	25	U,S	150 x 125	15	400
905D3S09X	905	55	U,S	230 x 225	22	600
905D3S12X	905	70	U,S	300 x 225	30	800
905D4S12X	905	90	U,S	300 x 340	30	800
905D4S16X	905	130	U,S	400 x 340	40	1200

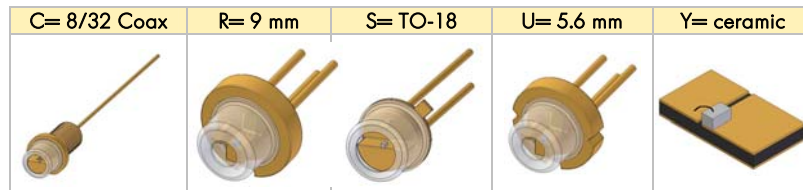
Option: C, R, Y package

905 nm Multi-junction devices

NEW

part number	Preliminary specifications (@ 21°C, 150 ns, 3,33 kHz)					
	wavelength	typ. power	package	emitting area	lop	lth
	nm	Watt		µm x µm	A	mA
905D1S3J03X	905	25	U,S	85 x 10	11	300
905D1S3J06X	905	50	U,S	160 x 10	22	500
905D1S3J09X	905	75	U,S	235 x 10	30	800
905D1S3J08X*	905	70	U,S	200 x 10	30	750
905D2S3J08X*	905	140	U,S	200 x 125	30	750
905D3S3J08X*	905	210	U,S	200 x 250	30	750

Option: C, R, Y package * (specifications @ 21°C, 100 ns, 1 kHz)



generic characteristics at 21°C				
	min	typ	max	units
wavelength	895	905	915	nm
spectral bandwidth		5		nm
temperature coefficient		0.27		nm/°C
beam spread				
	parallel to junction plane		12	degrees
reverse voltage			6	V
pulse duration				
	single element		1	µs
			200	ns
duty factor			0,1	%
temperature				
	storage	-55		°C
	operating	-45		°C

generic characteristics at 21°C				
	min	typ	max	units
wavelength	895	905	915	nm
spectral bandwidth		8		nm
temperature coefficient		0.28		nm/°C
beam spread				
	parallel		13	degrees
			20	degrees
reverse voltage			6	V
pulse duration				
	single element		150	ns
			100	ns
duty factor			0.1	%
temperature				
	storage	-55		°C
	operating	-45		°C

PULSED LASER DIODES

1550 nm

part number	specifications (@ 21°C, 150 ns, duty factor= 0.1%)					
	wavelength	min power	package	emitting area	lop	lth
	nm	Watt		µm x µm	A	A
155G1S02X	1550	3	S	50 x 1	10	0.4
155G1S06X	1550	5	S	150 x 1	20	1
155G1S14X	1550	12	S	350 x 1	40	1.5
155G2S06X	1550	10	S	150 x 150	20	1
155G4S14X	1550	45	S	350 x 340	40	1.5

Option: R, Y package

1550 nm, Multi-junction devices

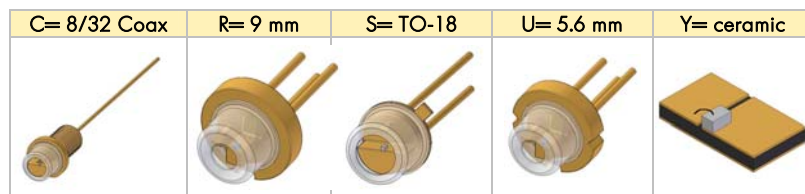
NEW

part number	specifications (@ 21°C, 150 ns, duty factor= 0.1%)					
	wavelength	min power	package	emitting area	lop	lth
	nm	Watt		µm x µm	A	A
155G1S2J02X	1550	5	S	50 x 7	10	0.4

1550 nm, High Intensity

part number	specifications (@ 21°C, 150 ns, duty factor= 0.1%)					
	wavelength	typ. power	package	emitting area	lop	lth
	nm	Watt		µm x µm	A	A
HI155G1S02X	1525	7	S	50 x 1	20	0.3
HI155G1S04X	1525	10	S	100 x 1	26	0.6
HI155G1S06X	1525	12	S	150 x 1	30	0.9
HI155G1S14X	1525	25	S	350 x 1	60	2

Option: R, Y package



generic characteristics at 21°C				
	min	typ	max	units
wavelength	1520	1550	1580	nm
spectral bandwidth		12		nm
temperature coefficient		0.5		nm/°C
beam spread				
parallel to junction plane		10		degrees
perpendicular				
single element		30		degrees
stacks		30		degrees
reverse voltage			2	V
pulse duration				
single element			200	ns
stacks			150	ns
duty factor			0.1	%
temperature				
storage	-55		100	°C
operating	-45		85	°C

generic characteristics at 21°C				
	min	typ	max	units
wavelength	1500	1525	1580	nm
spectral bandwidth		25		nm
temperature coefficient		0.35	0.7	nm/°C
beam spread				
parallel to junction plane		12		degrees
perpendicular		25		degrees
reverse voltage			6	V
pulse duration			150	ns
duty factor			0.1	%
temperature				
storage	-55		100	°C
operating	-45		85	°C